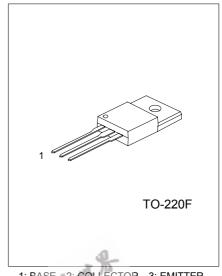
UTC 2SA1837 PNP EPITAXIAL SILICON TRANSISTOR

POWER AMPLIFIER APPLICATIONS DRIVER STAGE **AMPLIFIER APPLICATIONS**

FEATURES

- * High Transition Frequency: f_T =70MH $_Z$ (Typ.)
- * Complementary to UTC 2SC4793



1: BASE 2: COLLECTOR 3: EMITTER

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

, 12002012 11, 0 11110111 1 0 11 11 100 (11	u _00)		
PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V _{CBO}	-230	V
Collector-Emitter Voltage	V _{CEO}	-230	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	Ic	-1	Α
Base Current	l _B	-0.1	Α
Collector Power Dissipation Ta=25℃ Tc=25℃	P _C	2.0 20	W
Junction Temperature	T_J	150	$^{\circ}$
Storage Temperature Range	Tstg	-55 ~ 150	$^{\circ}\mathbb{C}$

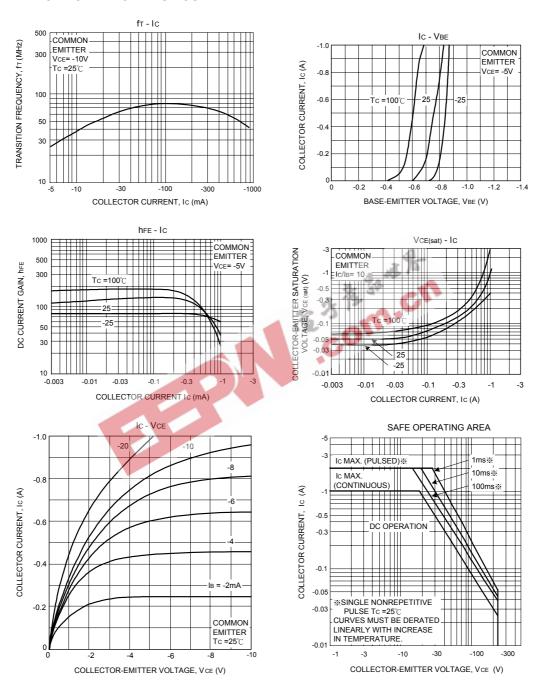
ELECTRICAL CHARACTERISTICS (Ta=25°C)

SYMBOL	TEAT AGNIDITIONS				
CTIVIDOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$	I_C = -10mA, I_B =0	-230			V
I _{CBO}	$V_{CB} = -230V, I_{E} = 0$			-1.0	μA
I _{EBO}	$V_{EB} = -5V, I_{C} = 0$			-1.0	μA
h_{FE}	V_{CE} = -5V, I_{C} = -100mA	100		320	
V _{CE (sat)}	I _C = -500mA _, I _B = -50mA			-1.5	V
V_{BE}	V_{CE} = -5V, I_{C} = -500mA			-1.0	V
fτ	V _{CE} = -10V, I _C = -100mA		70		MHz
Cob	V _{CB} = -10V, I _C =0, f=1MHz		30		pF
	V _(BR) CEO ICBO IEBO hFE VCE (sat) VBE fT	$\begin{array}{lll} V_{(BR)CEO} & I_{CE} - 10mA, \ I_{B} = 0 \\ I_{CBO} & V_{CB} = -230V, \ I_{E} = 0 \\ I_{EBO} & V_{EB} = -5V, \ I_{C} = 0 \\ h_{FE} & V_{CE} = -5V, \ I_{C} = -100mA \\ V_{CE(sat)} & I_{C} = -500mA, \ I_{B} = -50mA \\ V_{BE} & V_{CE} = -5V, \ I_{C} = -500mA \\ f_{T} & V_{CE} = -10V, \ I_{C} = -100mA \\ \end{array}$	$\begin{array}{c} V_{(BR)CEO} & I_{C}{=} -10 mA, \ I_{B}{=}0 & -230 \\ I_{CBO} & V_{CB}{=} -230 V, \ I_{E}{=}0 \\ I_{EBO} & V_{EB}{=} -5 V, \ I_{C}{=}0 \\ h_{FE} & V_{CE}{=} -5 V, \ I_{C}{=} -100 mA & 100 \\ V_{CE(sat)} & I_{C}{=} -500 mA, \ I_{B}{=} -50 mA \\ V_{BE} & V_{CE}{=} -5 V, \ I_{C}{=} -500 mA \\ f_{T} & V_{CE}{=} -10 V, \ I_{C}{=} -100 mA \\ \end{array}$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

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TYPICAL CHARACTERISTICS



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